

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF10350** is Designed for TCAS/TACAN Applications up to 1090 MHz.

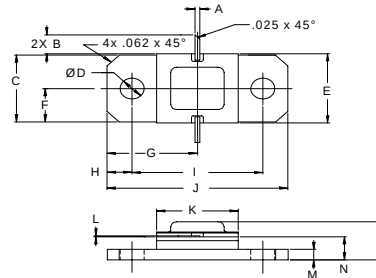
FEATURES:

- Internal Input Matching Network
- $P_G = 8.5$ dB at 350 W/1090 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	31 A
V_{CBO}	65 V
V_{CES}	65 V
P_{DISS}	1590 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	0.11°C/W

PACKAGE STYLE .400 2NL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.004 / 0.10	.007 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.118 / 3.00	.131 / 3.33
P		.230 / 5.84

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 60$ mA	65			V
BV_{CES}	$I_C = 60$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CBO}	$V_{CE} = 36$ V			25	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 5.0$ A	20			---
P_G η_c	$V_{CC} = 50$ V $P_{OUT} = 350$ W $f = 1090$ MHz	8.5 40	9.0		dB %